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The optical properties of GaAs<sub>1-x</sub>N<sub>x</sub> with x up to 2.5% grown by metalorganic chemical vapor deposition on GaAs(001) substrates are reported. Fundamental band gaps are obtained by photoreflectance measurements. Room-temperature pseudodielectric functions obtained by spectroscopic ellipsometry in the range from 2.7 to 5.2 eV are modeled with a three-phase structure that accounts for the GaAs<sub>1-x</sub>N<sub>x</sub> layer, native oxide, and ambient. We employ **Adachi**'s critical-point composite model for the parametrization of GaAs<sub>1-x</sub>N<sub>x</sub>, and the compositional dependence of critical-point energies is obtained. While the energy of  $E_0$  decreases with x, those of  $E_1$  and  $E_1+\Delta_1$  increase with x. This fact, somewhat anomalous compared with conventional III-V alloys, indicates that the lowest-lying conduction bands along  $\langle 111 \rangle$  directions may be perturbed by the incorporated nitrogen.

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